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REVISION HISTORY

10/06—Rev. B to Rev. C

Changes to Table 4.....	9
Changes to Ordering Guide	18

12/04—Rev. A to Rev. B

Updated Format.....	Universal
Changes to Specifications Section	3
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Updated Outline Dimensions	16
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2/98—Rev. 0 to Rev. A

10/97—Revision 0: Initial Version

PRODUCT HIGHLIGHTS

1. Low R_{ON} (5 Ω maximum).
2. Ultralow Power Dissipation.
3. Extended Signal Range.
The ADG451/ADG452/ADG453 are fabricated on an enhanced LC²MOS process, giving an increased signal range that fully extends to the supply rails.
4. Break-Before-Make Switching.
This prevents channel shorting when the switches are configured as a multiplexer (ADG453 only.)
5. Single-Supply Operation.
For applications in which the analog signal is unipolar, the ADG451/ADG452/ADG453 can be operated from a single rail power supply. The parts are fully specified with a single 12 V power supply and remain functional with single supplies as low as 5.0 V.
6. Dual-Supply Operation.
For applications where the analog signal is bipolar, the ADG451/ADG452/ADG453 can be operated from a dual power supply ranging from ± 4.5 V to ± 20 V.

ADG451/ADG452/ADG453

SPECIFICATIONS

15 V DUAL SUPPLY

$V_{DD} = 15\text{ V}$, $V_{SS} = -15\text{ V}$, $V_L = 5\text{ V}$, $GND = 0\text{ V}$. All specifications T_{MIN} to T_{MAX} , unless otherwise noted.

Table 1.

Parameter	B Version ¹		Unit	Test Conditions/Comments
	25°C	T _{MIN} to T _{MAX}		
ANALOG SWITCH				
Analog Signal Range		V _{SS} to V _{DD}	V	
On Resistance (R _{ON})	4		Ω typ	V _D = −10 V to +10 V, I _S = −10 mA
	5	7	Ω max	
On Resistance Match Between Channels (ΔR _{ON})	0.1		Ω typ	V _D = ±10 V, I _S = −10 mA
	0.5	0.5	Ω max	
On Resistance Flatness (R _{FLAT(ON)})	0.2		Ω typ	V _D = −5 V, 0 V, +5 V, I _S = −10 mA
	0.5	0.5	Ω max	
LEAKAGE CURRENTS ²				
Source Off Leakage, I _S (OFF)	±0.02		nA typ	V _D = ±10 V, V _S = ±10 V; see Figure 17
	±0.5	±2.5	nA max	
Drain Off Leakage, I _D (OFF)	±0.02		nA typ	V _D = ±10 V, V _S = ±10 V; see Figure 17
	±0.5	±2.5	nA max	
Channel On Leakage, I _D , I _S (ON)	±0.04		nA typ	V _D = V _S = ±10 V; see Figure 18
	±1	±5	nA max	
DIGITAL INPUTS				
Input High Voltage, V _{INH}		2.4	V min	
Input Low Voltage, V _{INL}		0.8	V max	
Input Current, I _{INL} or I _{INH}	0.005		μA typ	V _{IN} = V _{INL} or V _{INH} ; all others = 2.4 V or 0.8 V, respectively
		±0.5	μA max	
DYNAMIC CHARACTERISTICS ³				
t _{ON}	70		ns typ	R _L = 300 Ω, C _L = 35 pF, V _S = ±10 V; see Figure 19
	180	220	ns max	
t _{OFF}	60		ns typ	R _L = 300 Ω, C _L = 35 pF, V _S = ±10 V; see Figure 19
	140	180	ns max	
Break-Before-Make Time Delay, t _D (ADG453 Only)	15		ns typ	R _L = 300 Ω, C _L = 35 pF, V _{S1} = V _{S2} = +10 V; see Figure 20
	5	5	ns min	
Charge Injection	20		pC typ	V _S = 0 V, R _S = 0 Ω, C _L = 1.0 nF; see Figure 21
	30		pC max	
Off Isolation	65		dB typ	R _L = 50 Ω, C _L = 5 pF, f = 1 MHz; see Figure 22
Channel-to-Channel Crosstalk	−90		dB typ	R _L = 50 Ω, C _L = 5 pF, f = 1 MHz; see Figure 23
C _S (OFF)	37		pF typ	f = 1 MHz
C _D (OFF)	37		pF typ	f = 1 MHz
C _D , C _S (ON)	140		pF typ	f = 1 MHz
POWER REQUIREMENTS				
I _{DD}	0.0001		μA typ	V _{DD} = 16.5 V, V _{SS} = −16.5 V; digital inputs = 0 V or 5 V
	0.5	5	μA max	
I _{SS}	0.0001		μA typ	
	0.5	5	μA max	
I _L	0.0001		μA typ	
	0.5	5	μA max	
I _{GND} ³	0.0001		μA typ	
	0.5	5	μA max	

¹ Temperature range for B version is -40°C to $+85^\circ\text{C}$.

² $T_{MAX} = 70^\circ\text{C}$.

³ Guaranteed by design, not subject to production test.

12 V SINGLE SUPPLY

$V_{DD} = 12\text{ V}$, $V_{SS} = 0\text{ V}$, $V_L = 5\text{ V}$, $GND = 0\text{ V}$. All specifications T_{MIN} to T_{MAX} , unless otherwise noted.

Table 2.

Parameter	B Version ¹		Unit	Test Conditions/Comments
	25°C	T _{MIN} to T _{MAX}		
ANALOG SWITCH				
Analog Signal Range		0 V to V _{DD}	V	
On Resistance (R _{ON})	6		Ω typ	V _D = 0 V to +10 V, I _S = −10 mA
	8	10	Ω max	
On Resistance Match Between Channels (ΔR _{ON})	0.1		Ω typ	V _D = 10 V, I _S = −10 mA
	0.5	0.5	Ω max	
On Resistance Flatness (R _{FLAT(ON)})	1.0	1.0	Ω typ	V _D = 0 V, 5 V, I _S = −10 mA
LEAKAGE CURRENTS ^{2, 3}				
Source Off Leakage, I _S (OFF)	±0.02		nA typ	V _D = 0 V, 10 V, V _S = 0 V, 10 V; see Figure 17
	±0.5	±2.5	nA max	
Drain Off Leakage, I _D (OFF)	±0.02		nA typ	V _D = 0 V, 10 V, V _S = 0 V, 10 V; see Figure 17
	±0.5	±2.5	nA max	
Channel On Leakage, I _D , I _S (ON)	±0.04		nA typ	V _D = V _S = 0 V, 10 V; see Figure 18
	±1	±5	nA max	
DIGITAL INPUTS				
Input High Voltage, V _{INH}		2.4	V min	
Input Low Voltage, V _{INL}		0.8	V max	
Input Current, I _{INL} or I _{INH}	0.005		μA typ	V _{IN} = V _{INL} or V _{INH}
		±0.5	μA max	
DYNAMIC CHARACTERISTICS ⁴				
t _{ON}	100		ns typ	R _L = 300 Ω, C _L = 35 pF, V _S = 8 V; see Figure 19
	220	260	ns max	
t _{OFF}	80		ns typ	R _L = 300 Ω, C _L = 35 pF, V _S = 8 V; see Figure 19
	160	200	ns max	
Break-Before-Make Time Delay, t _D (ADG453 Only)	15		ns typ	R _L = 300 Ω, C _L = 35 pF, V _{S1} = V _{S2} = 8 V; see Figure 20
	10	10	ns min	
Charge Injection	10		pC typ	V _S = 6 V, R _S = 0 Ω, C _L = 1.0 nF; see Figure 21
Channel-to-Channel Crosstalk	−90		dB typ	R _L = 50 Ω, C _L = 5 pF, f = 1 MHz; see Figure 23
C _S (OFF)	60		pF typ	f = 1 MHz
C _D (OFF)	60		pF typ	f = 1 MHz
C _D , C _S (ON)	100		pF typ	f = 1 MHz
POWER REQUIREMENTS				
I _{DD}	0.0001		μA typ	V _{DD} = 13.2 V; digital inputs = 0 V or 5 V
	0.5	5	μA max	
I _L	0.0001		μA typ	
	0.5	5	μA max	V _L = 5.5 V
I _{GND} ⁴	0.0001		μA typ	
	0.5	5	μA max	V _L = 5.5 V

¹ Temperature range for B version is -40°C to $+85^\circ\text{C}$.

² $T_{MAX} = 70^\circ\text{C}$.

³ Tested with dual supplies.

⁴ Guaranteed by design, not subject to production test.

ADG451/ADG452/ADG453

5 V DUAL SUPPLY

$V_{DD} = +5$ V, $V_{SS} = -5$ V, $V_L = +5$ V, GND = 0 V. All specifications T_{MIN} to T_{MAX} , unless otherwise noted.

Table 3.

Parameter	B Version ¹		Unit	Test Conditions/Comments
	25°C	T _{MIN} to T _{MAX}		
ANALOG SWITCH				
Analog Signal Range		V _{SS} to V _{DD}	V	
On Resistance (R _{ON})	7		Ω typ	V _D = −3.5 V to +3.5 V, I _S = −10 mA
	12	15	Ω max	
On Resistance Match Between Channels (ΔR _{ON})	0.3		Ω typ	V _D = 3.5 V, I _S = −10 mA
	0.5	0.5	Ω max	
LEAKAGE CURRENTS ^{2, 3}				
Source Off Leakage, I _S (OFF)	±0.02		nA typ	V _D = ±4.5, V _S = ±4.5; see Figure 17
	±0.5	±2.5	nA max	
Drain Off Leakage, I _D (OFF)	±0.02		nA typ	V _D = 0 V, 5 V, V _S = 0 V, 5 V; see Figure 17
	±0.5	±2.5	nA max	
Channel On Leakage, I _D , I _S (ON)	±0.04		nA typ	V _D = V _S = 0 V, 5 V; see Figure 18
	±1	±5	nA max	
DIGITAL INPUTS				
Input High Voltage, V _{INH}		2.4	V min	
Input Low Voltage, V _{INL}		0.8	V max	
Input Current, I _{INL} or I _{INH}	0.005		μA typ	V _{IN} = V _{INL} or V _{INH}
		±0.5	μA max	
DYNAMIC CHARACTERISTICS ⁴				
t _{ON}	160		ns typ	R _L = 300 Ω, C _L = 35 pF, V _S = 3 V; see Figure 19
	220	300	ns max	
t _{OFF}	60		ns typ	R _L = 300 Ω, C _L = 35 pF, V _S = 3 V; see Figure 19
	140	180	ns max	
Break-Before-Make Time Delay, t _D (ADG453 Only)	50		ns typ	R _L = 300 Ω, C _L = 35 pF, V _{S1} = V _{S2} = 3 V; see Figure 20
	5	5	ns min	
Charge Injection	10		pC typ	V _S = 0 V, R _S = 0 Ω, C _L = 1.0 nF; see Figure 21
Off Isolation	65		dB typ	R _L = 50 Ω, C _L = 5 pF, f = 1 MHz; see Figure 22
Channel-to-Channel Crosstalk	−76		dB typ	R _L = 50 Ω, C _L = 5 pF, f = 1 MHz; see Figure 23
C _S (OFF)	48		pF typ	f = 1 MHz
C _D (OFF)	48		pF typ	f = 1 MHz
C _D , C _S (ON)	148		pF typ	f = 1 MHz
POWER REQUIREMENTS				
I _{DD}	0.0001		μA typ	V _{DD} = 5.5 V; digital inputs = 0 V or 5 V
	0.5	5	μA max	
I _{SS}	0.0001		μA typ	
	0.5	5	μA max	
I _L	0.0001		μA typ	
	0.5	5	μA max	V _L = 5.5 V
I _{GND} ⁴	0.0001		μA typ	
	0.5	5	μA max	V _L = 5.5 V

¹ Temperature range for B version is -40°C to $+85^\circ\text{C}$.

² $T_{MAX} = 70^\circ\text{C}$.

³ Tested with dual supplies.

⁴ Guaranteed by design, not subject to production test.

ABSOLUTE MAXIMUM RATINGS

$T_A = 25^\circ\text{C}$, unless otherwise noted.

Table 4.

Parameters	Ratings
V_{DD} to V_{SS}	44 V
V_{DD} to GND	$-0.3\text{ V to }+32\text{ V}$
V_{SS} to GND	$+0.3\text{ V to }-32\text{ V}$
V_L to GND	$-0.3\text{ V to }V_{DD} + 0.3\text{ V}$
Analog, Digital Inputs ¹	$V_{SS} - 2\text{ V to }V_{DD} + 2\text{ V}$ or 30 mA, whichever occurs first
Continuous Current, S or D	100 mA
Peak Current, S or D (pulsed at 1 ms, 10% duty cycle maximum)	300 mA
Operating Temperature Range	
Industrial (B Version)	$-40^\circ\text{C to }+85^\circ\text{C}$
Storage Temperature Range	$-65^\circ\text{C to }+150^\circ\text{C}$
Junction Temperature	150°C
Plastic DIP Package, Power Dissipation	470 mW
θ_{JA} Thermal Impedance	117°C/W
Lead Temperature, Soldering (10 sec)	260°C
SOIC Package, Power Dissipation	600 mW
θ_{JA} Thermal Impedance	77°C/W
TSSOP Package, Power Dissipation	450 mW
θ_{JA} Thermal Impedance	115°C/W
θ_{JC} Thermal Impedance	35°C/W
Lead Temperature, Soldering	
Vapor Phase (60 sec)	215°C
Infrared (15 sec)	220°C
ESD	2 kV

¹ Overvoltages at IN, S, or D are clamped by internal diodes. Current should be limited to the maximum ratings given.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those listed in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Only one absolute maximum rating may be applied at any one time.

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

ADG451/ADG452/ADG453

PIN CONFIGURATION AND FUNCTION DESCRIPTIONS

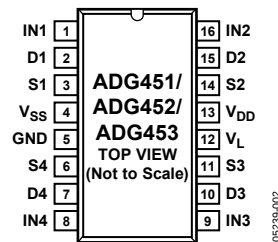


Figure 4. Pin Configuration

Table 5. Pin Function Descriptions

Pin No.	Mnemonic	Description
1	IN1	Logic Control Input.
2	D1	Drain Terminal. Can be an input or an output.
3	S1	Source Terminal. Can be an input or an output.
4	V _{SS}	Most Negative Power Supply Potential in Dual Supplies. In single-supply applications, it can be connected to GND.
5	GND	Ground (0 V) Reference.
6	S4	Source Terminal. Can be an input or an output.
7	D4	Drain Terminal. Can be an input or an output.
8	IN4	Logic Control Input.
9	IN3	Logic Control Input.
10	D3	Drain Terminal. Can be an input or an output.
11	S3	Source Terminal. Can be an input or an output.
12	V _L	Logic Power Supply (5 V).
13	V _{DD}	Most Positive Power Supply Potential.
14	S2	Source Terminal. Can be an input or an output.
15	D2	Drain Terminal. Can be an input or an output.
16	IN2	Logic Control Input.

Table 6. Truth Table (ADG451/ADG452)

ADG451 In	ADG452 In	Switch Condition
0	1	On
1	0	Off

Table 7. Truth Table (ADG453)

Logic	Switch 1, Switch 4	Switch 2, Switch 3
0	Off	On
1	On	Off

TYPICAL PERFORMANCE CHARACTERISTICS

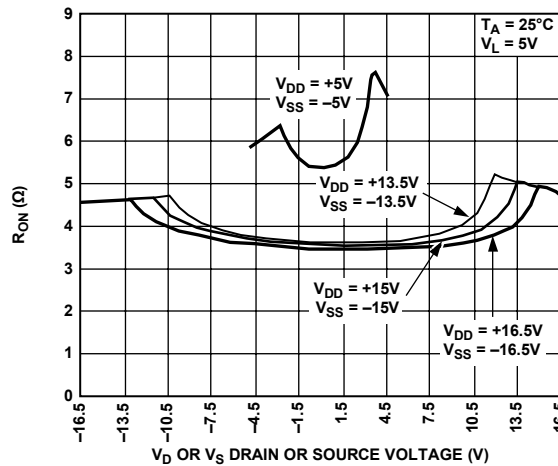


Figure 5. On Resistance as a Function of V_D (V_S) for Various Dual Supplies

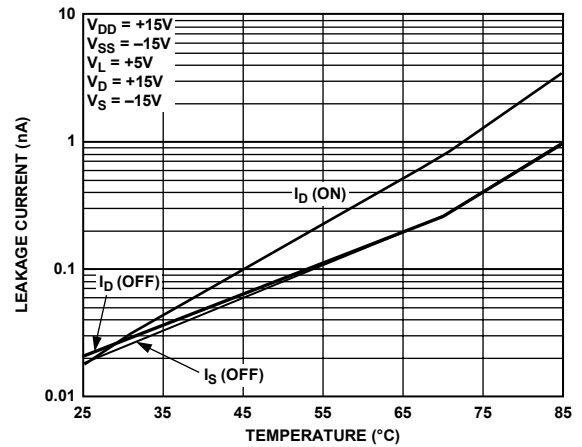


Figure 8. Leakage Currents as a Function of Temperature

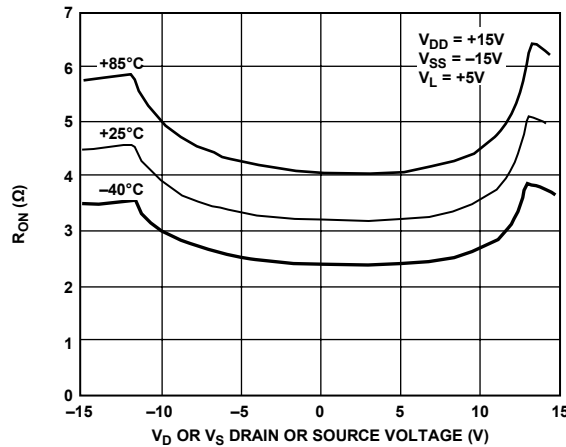


Figure 6. On Resistance as a Function of V_D (V_S) for Different Temperatures with Dual Supplies

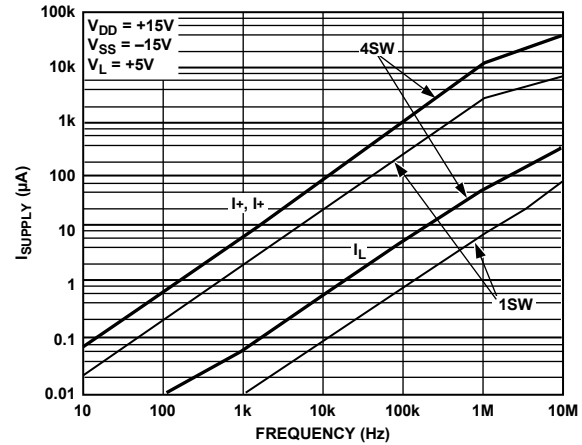


Figure 9. Supply Current vs. Input Switching Frequency

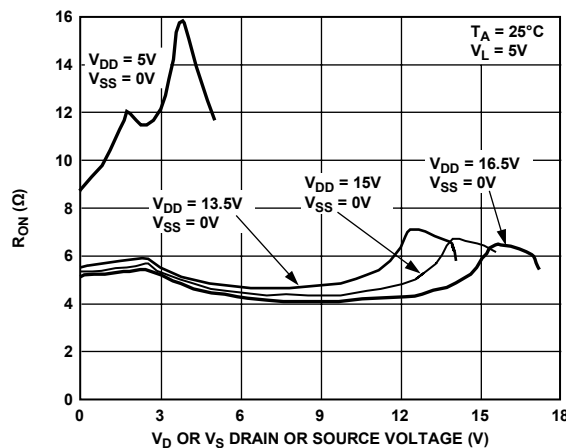


Figure 7. On Resistance as a Function of V_D (V_S) for Various Single Supplies

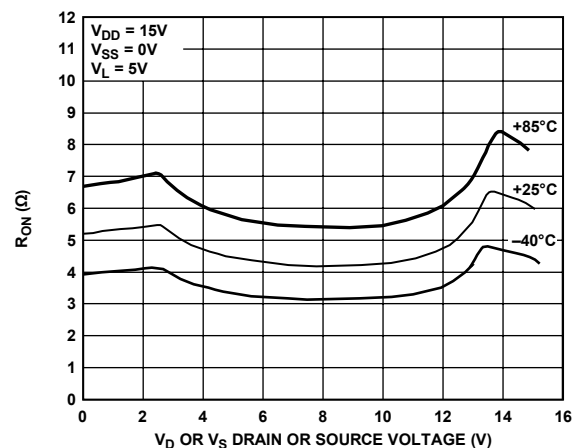


Figure 10. On Resistance as a Function of V_D (V_S) for Different Temperatures with Single Supplies

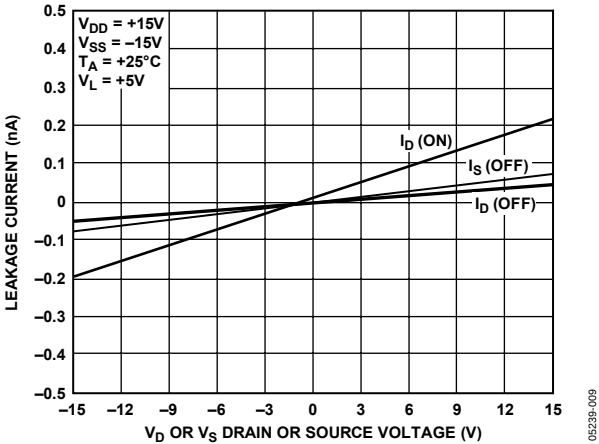


Figure 11. Leakage Currents as a Function of V_D (V_S)

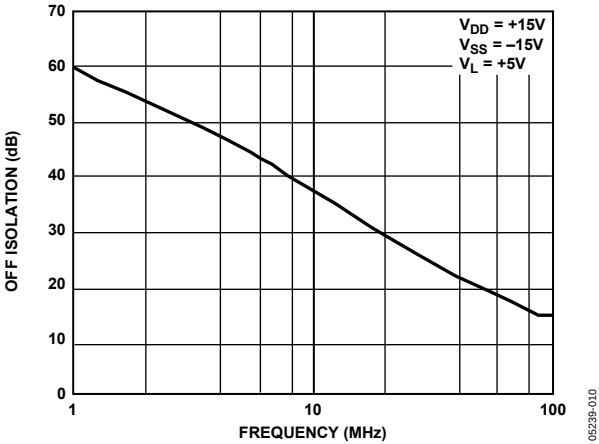


Figure 12. Off Isolation vs. Frequency

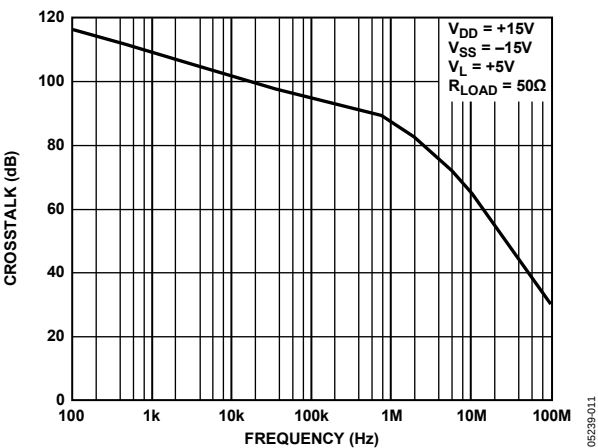


Figure 13. Crosstalk vs. Frequency

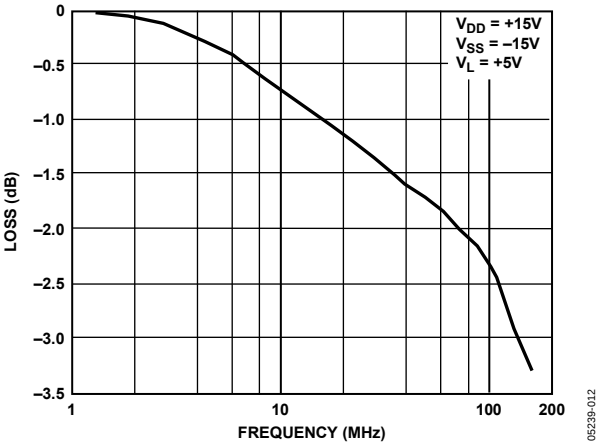


Figure 14. Frequency Response with Switch On

TERMINOLOGY

R_{ON}

Ohmic resistance between D and S.

ΔR_{ON}

On resistance match between any two channels, that is, R_{ON} maximum minus R_{ON} minimum.

$R_{FLAT(ON)}$

Flatness is defined as the difference between the maximum and minimum value of on resistance, as measured over the specified analog signal range.

I_S (OFF)

Source leakage current with the switch off.

I_D (OFF)

Drain leakage current with the switch off.

I_D, I_S (ON)

Channel leakage current with the switch on.

V_D (V_S)

Analog voltage on Terminal D and Terminal S.

C_S (OFF)

Off switch source capacitance.

C_D (OFF)

Off switch drain capacitance.

C_D (ON), C_S (ON)

On switch capacitance.

t_{ON}

Delay between applying the digital control input and the output switching on. See Figure 19.

t_{OFF}

Delay between applying the digital control input and the output switching off.

t_D

Off time or on time measured between the 90% points of both switches, when switching from one address state to another. See Figure 20.

Crosstalk

A measure of unwanted signal coupled through from one channel to another as a result of parasitic capacitance.

Off Isolation

A measure of unwanted signal coupling through an off switch.

Charge Injection

A measure of the glitch impulse transferred from the digital input to the analog output during switching.

APPLICATIONS

Figure 15 illustrates a precise, fast, sample-and-hold circuit. An [AD845](#) is used as the input buffer, and the output operational amplifier is an [AD711](#). During track mode, SW1 is closed, and the output, V_{OUT} , follows the input signal, V_{IN} . In hold mode, SW1 is opened, and the signal is held by the hold capacitor, C_H .

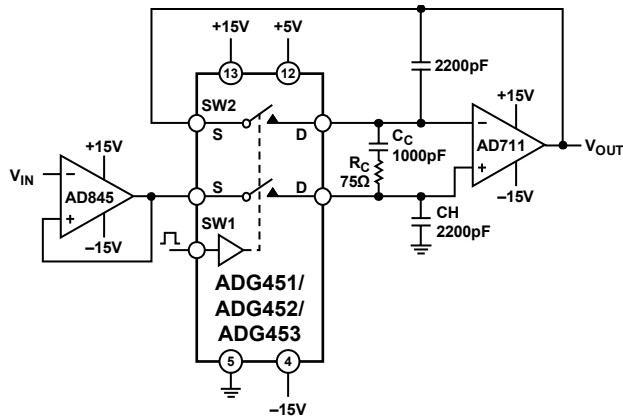


Figure 15. Fast, Accurate Sample-and-Hold Circuit

Due to switch and capacitor leakage, the voltage on the hold capacitor decreases with time. The ADG451/ADG452/ADG453 minimize this droop due to their low leakage specifications. The droop rate is further minimized by the use of a polystyrene hold capacitor. The droop rate for the circuit shown is typically $30 \mu\text{V}/\mu\text{s}$.

A second switch, SW2, which operates in parallel with SW1, is included in this circuit to reduce pedestal error. Because both switches are at the same potential, they have a differential effect on the op amp, AD711, which minimizes charge injection effects. Pedestal error is also reduced by the compensation network, R_C and C_C . This compensation network reduces the hold time glitch while optimizing the acquisition time. Using the illustrated op amps and component values, the pedestal error has a maximum value of 5 mV over the $\pm 10 \text{ V}$ input range. Both the acquisition and settling times are 850 ns.

05239-013

TEST CIRCUITS

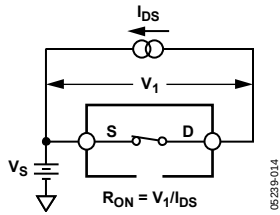


Figure 16. On Resistance

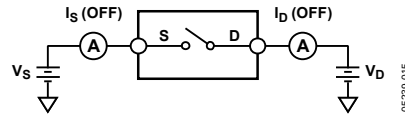


Figure 17. Off Leakage

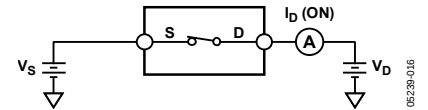


Figure 18. On Leakage

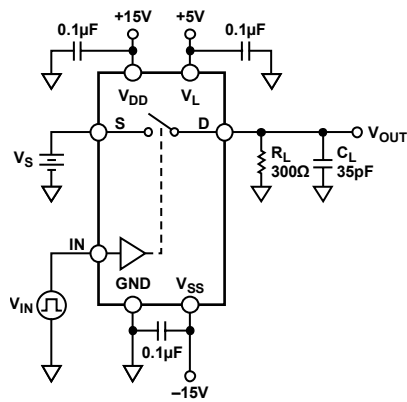


Figure 19. Switching Times

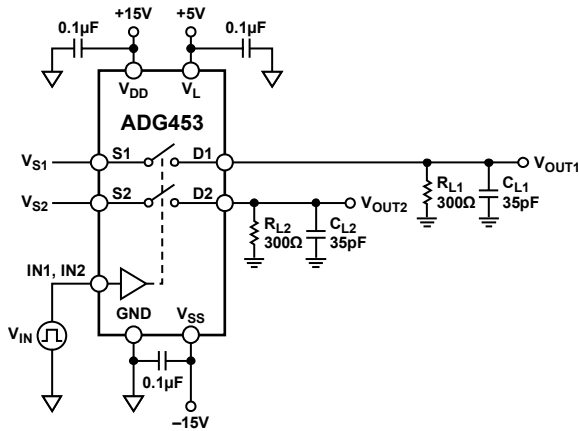
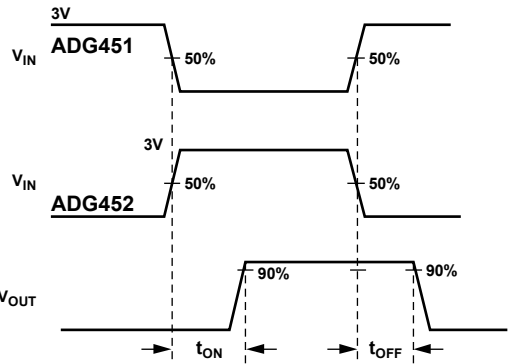


Figure 20. Break-Before-Make Time Delay

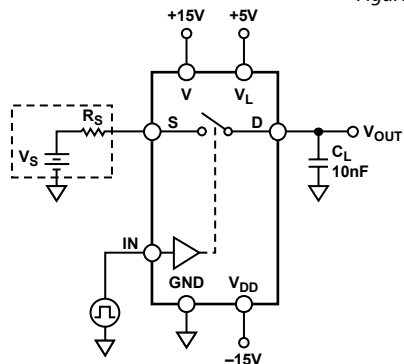
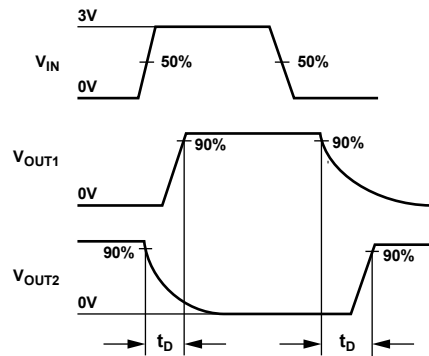
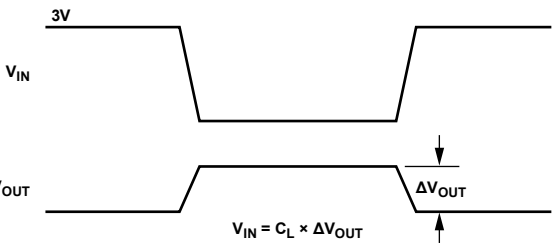


Figure 21. Charge Injection



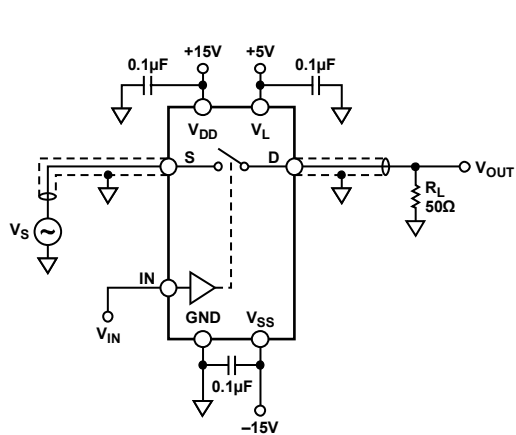
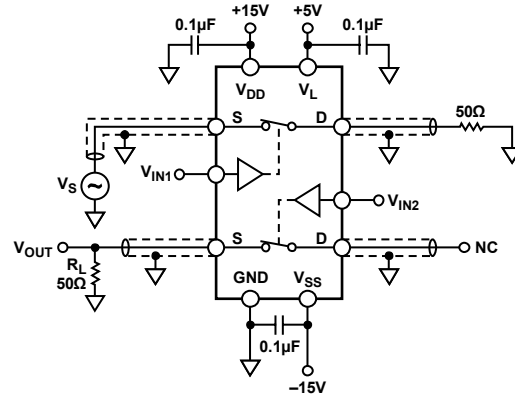


Figure 22. Off Isolation

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$$\text{CHANNEL-TO-CHANNEL CROSSTALK} = 20 \times \log |V_S/V_{OUT}|$$

Figure 23. Channel-to-Channel Crosstalk

05239-021

OUTLINE DIMENSIONS

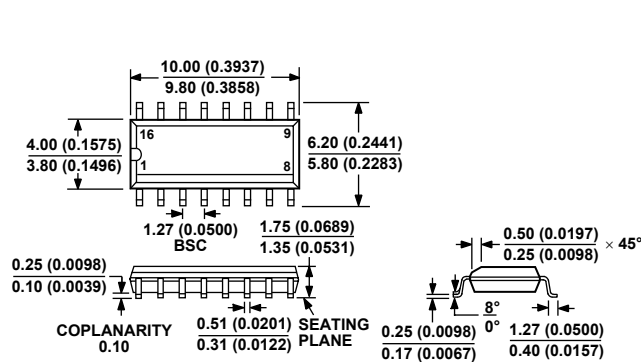


Figure 24. 16-Lead Standard Small Outline Package [SOIC_N]
Narrow Body
(R-16)
Dimensions shown in millimeters and (inches)

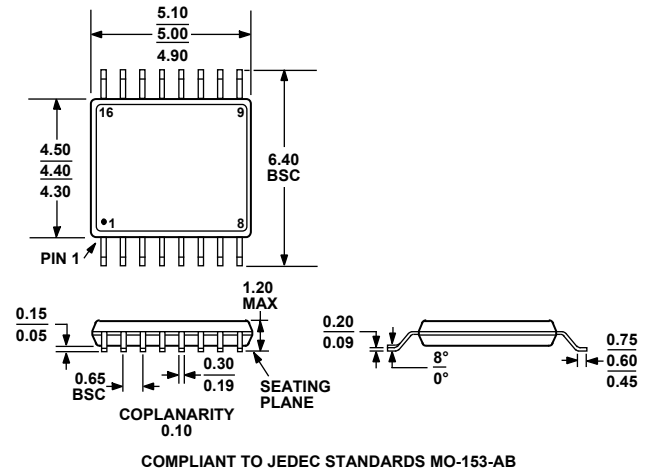


Figure 25. 16-Lead Thin Shrink Small Outline Package [TSSOP]
(RU-16)
Dimensions shown in millimeters

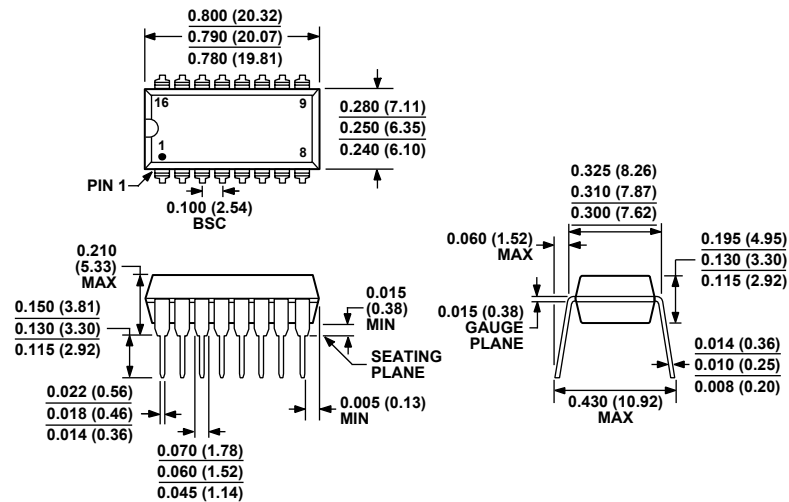


Figure 26. 16-Lead Plastic Dual In-Line Package [PDIP]
Narrow Body
(N-16)
Dimensions shown in inches and (millimeters)

ADG451/ADG452/ADG453

ORDERING GUIDE

Model	Temperature Range	Package Description	Package Option
ADG451BN	−40°C to +85°C	16-Lead Plastic Dual In-Line Package [PDIP]	N-16
ADG451BNZ ¹	−40°C to +85°C	16-Lead Plastic Dual In-Line Package [PDIP]	N-16
ADG451BR	−40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG451BR-REEL	−40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG451BR-REEL7	−40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG451BRZ ¹	−40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG451BRZ-REEL ¹	−40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG451BRZ-REEL7 ¹	−40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG451BRUZ ¹	−40°C to +85°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG451BRUZ-REEL ¹	−40°C to +85°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG451BRUZ-REEL7 ¹	−40°C to +85°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG451BCHIPS		DIE	
ADG452BN	−40°C to +85°C	16-Lead Plastic Dual In-Line Package [PDIP]	N-16
ADG452BNZ ¹	−40°C to +85°C	16-Lead Plastic Dual In-Line Package [PDIP]	N-16
ADG452BR	−40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG452BR-REEL	−40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG452BR-REEL7	−40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG452BRZ ¹	−40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG452BRZ-REEL ¹	−40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG452BRZ-REEL7 ¹	−40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG452BRUZ ¹	−40°C to +85°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG452BRUZ-REEL ¹	−40°C to +85°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG452BRUZ-REEL7 ¹	−40°C to +85°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG453BN	−40°C to +85°C	16-Lead Plastic Dual In-Line Package [PDIP]	N-16
ADG453BNZ ¹	−40°C to +85°C	16-Lead Plastic Dual In-Line Package [PDIP]	N-16
ADG453BR	−40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG453BR-REEL	−40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG453BR-REEL7	−40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG453BRZ ¹	−40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG453BRZ-REEL ¹	−40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG453BRZ-REEL7 ¹	−40°C to +85°C	16-Lead Standard Small Outline Package [SOIC_N]	R-16
ADG453BRUZ ¹	−40°C to +85°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG453BRUZ-REEL ¹	−40°C to +85°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG453BRUZ-REEL7 ¹	−40°C to +85°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16

¹ Z = Pb-free part.